

## ISL28133

Single Micropower, Chopper Stabilized, RRIO Operational Amplifier

FN6560 Rev.7.1 Apr 22, 2021

The <u>ISL28133</u> is a single micropower, chopper stabilized operational amplifier that is optimized for single supply operation from 1.8V to 5.5V. Its low supply current of  $18\mu A$  and wide input range enable make it an excellent general purpose op amp for a range of applications. The ISL28133 is ideal for handheld devices that operate off 2 AA or single Li-ion batteries.

The ISL28133 is available in the 5 Ld SOT-23 and 5 Ld SC70 packages. All devices operate over the extended temperature range of -40  $^{\circ}$ C to +125  $^{\circ}$ C.

## **Features**

•	Low input offset voltage	8μν	, Max
•	Low offset TC	0.075μV/°0	C, Max
•	Input bias current	300pA	, Max
•	Quiescent current	18µ/	4, Тур
•	Wide supply range	1.8V t	o 5.5\
•	Low noise (0.01Hz to 10Hz)	1.1µV <sub>P-</sub>	<sub>P</sub> , Typ
•	Rail-to-rail inputs and output		
•	Operating temperature range	40°C to +1	L25°(

## **Applications**

- · Bidirectional current sense
- Temperature measurement
- · Medical equipment
- · Electronic weigh scales

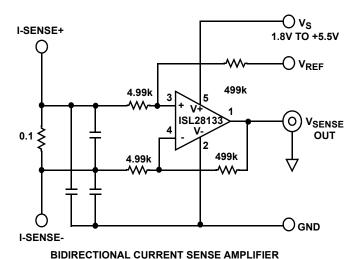


FIGURE 1. TYPICAL APPLICATION CIRCUIT

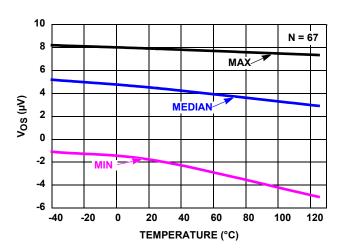
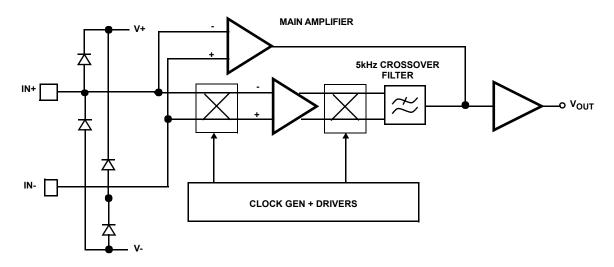


FIGURE 2. VOS vs TEMPERATURE

## **Block Diagram**



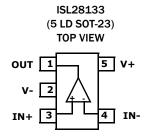
# **Ordering Information**

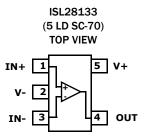
PART NUMBER	PART MARKING	PACKAGE DESCRIPTION (RoHS Compliant)	PKG. DWG. #	CARRIER TYPE (Note 1)
ISL28133FHZ-T7 (Note 2)	BCFA (Note 5)	5 Ld SOT-23	P5.064A	Reel, 3k
ISL28133FHZ-T7A (Note 2)				Reel, 250
ISL28133FEZ-T7 (Note 2)	BHA (Note 5)	5 Ld SC70	P5.049	Reel, 3k
ISL28133ISENSEV1Z	Evaluation Board			
ISL28133EVAL1Z	Evaluation Board			
ISL28133CSENSEV1Z	Evaluation Board			

### NOTES:

- 1. See TB347 for details on reel specifications.
- These Pb-free plastic packaged products employ special Pb-free material sets, molding compounds/die attach materials, and 100% matte tin plate plus
  anneal (e3 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations). Pb-free products are MSL
  classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.
- These Pb-free plastic packaged products employ special Pb-free material sets; molding compounds/die attach materials and NiPdAu plate e4 termination
  finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Pb-free products are MSL classified at Pb-free peak reflow
  temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.
- For Moisture Sensitivity Level (MSL), please see the device information page for the <u>ISL28133</u>. For more information on MSL please see techbrief <u>TB363</u>.
- 5. The part marking is located on the bottom of the part.

# **Pin Configurations**





**TOP VIEW** 

# **Pin Descriptions**

ISL28133 (5 Ld SOT23)	ISL28133 (5 Ld SC-70)	PIN NAME	FUNCTION	EQUIVALENT CIRCUIT
3	1	IN+	Non-inverting input	IN+ CLOCK GEN + DRIVERS  Circuit 1
2	2	V-	Negative supply	
4	3	IN-	Inverting input	(See Circuit 1)
1	4	OUT	Output	V+ OUT Circuit 2
5	5	V+	Positive supply	

### **Absolute Maximum Ratings**

Max Supply Voltage V+ to V	6.5V
Max Voltage VIN to GND	-0.5V to 6.5V
Max Input Differential Voltage	6.5V
Max Input Current	20mA
Max Voltage VOUT to GND (10s)	6.5V
ESD Rating	
Human Body Model	3000V
Machine Model	200V
Charged Device Model	1500V

### **Thermal Information**

Thermal Resistance (Typical)	$\theta_{JA}$ (°C/W)	) θ <sub>JC</sub> (°C/W)
5 Ld SOT-23 (Note 6, 7)	225	110
5 Ld SC-70 (Note 6)	206	N/A
Maximum Storage Temperature Range		65°C to +150°C
Pb-Free Reflow Profile		see <u>TB493</u>

### **Operating Conditions**

Temperature Range	40°C to +125°C
Maximum Junction Temperature	140°C

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

#### NOTES:

- 6. θ<sub>JA</sub> is measured with the component mounted on a high effective thermal conductivity test board in free air. See <u>TB379</u> for details.
- 7. For  $\theta_{\mbox{\scriptsize JC}},$  the "case temp" location is taken at the package top center.

**Electrical Specifications**  $V_{+} = 5V$ ,  $V_{-} = 0V$ , VCM = 2.5V,  $T_{A} = +25$ °C,  $R_{L} = 0$ pen, unless otherwise specified. **Boldface limits apply** over the operating temperature range, -40°C to +125°C.

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 8)	TYP	MAX (Note 8)	UNIT
DC SPECIFICATIONS						
V <sub>OS</sub>	Input Offset Voltage		-8	±2	8	μV
			-15.5		15.5	μV
TCV <sub>OS</sub>	Input Offset Voltage Temperature Coefficient			0.02	0.075	μV/°C
I <sub>OS</sub>	Input Offset Current			-60		pA
I <sub>B</sub>	Input Bias Current		-300	±30	300	pA
			-600		600	pA
Common Mode Input Voltage Range		V+ = 5.0V, V- = GND	-0.1		5.1	V
CMRR	Common Mode Rejection Ratio	VCM = -0.1V to 5.0V	118	125		dB
			115			dB
PSRR	Power Supply Rejection Ratio	Vs = 2V to 5.5V	110	138		dB
			110			dB
V <sub>OH</sub>	Output Voltage Swing, High	$R_L = 10k\Omega$	4.965	4.981		V
V <sub>OL</sub>	Output Voltage Swing, Low	$R_L = 10k\Omega$		18	35	mV
A <sub>OL</sub>	Open Loop Gain	$R_L = 1M\Omega$		174		dB
V <sub>+</sub>	Supply Voltage	(Note 9)	1.8		5.5	V
I <sub>S</sub>	Supply Current	R <sub>L</sub> = OPEN		18	25	μΑ
					35	μΑ
I <sub>SC+</sub>	Output Source Short Circuit Current	R <sub>L</sub> = Short to ground or V+	13	17	26	mA
I <sub>SC-</sub>	Output Sink Short Circuit Current		-26	-19	-13	mA
AC SPECIFICATIONS			1			
GBWP	Gain Bandwidth Product f = 50kHz	$\begin{aligned} & \textbf{A}_{V} = \textbf{100},  \textbf{R}_{F} = \textbf{100} \textbf{k} \boldsymbol{\Omega}, \\ & \textbf{R}_{G} = \textbf{1} \textbf{k} \boldsymbol{\Omega},  \textbf{R}_{L} = \textbf{10} \textbf{k} \boldsymbol{\Omega}  \textbf{to}  \textbf{V}_{CM} \end{aligned}$		400		kHz
e <sub>N</sub> V <sub>P-P</sub>	Peak-to-Peak Input Noise Voltage	f = 0.01Hz to 10Hz		1.1		μV <sub>P-P</sub>
e <sub>N</sub>	Input Noise Voltage Density	f = 1kHz		65		nV/√(Hz)



**Electrical Specifications**  $V_{+} = 5V$ ,  $V_{-} = 0V$ , VCM = 2.5V,  $T_{A} = +25$  °C,  $R_{L} = 0$ pen, unless otherwise specified. **Boldface limits apply** over the operating temperature range, -40°C to +125°C. (Continued)

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 8)	TYP	MAX (Note 8)	UNIT
i <sub>N</sub>	Input Noise Current Density	f = 1kHz		72		fA/√(Hz)
		f = 10Hz		79		$fA/\sqrt{(Hz)}$
C <sub>in</sub>	Differential Input Capacitance	f = 1MHz		1.6		pF
	Common Mode Input Capacitance			1.12		pF
TRANSIENT RESPONS	E	<u>'</u>		1	l	1
SR	Positive Slew Rate	$V_{OUT}$ = 1V to 4V, $R_L$ = 10k $\Omega$		0.2		V/µs
	Negative Slew Rate			0.1		V/µs
t <sub>r</sub> , t <sub>f</sub> , Small Signal	Rise Time, t <sub>r</sub> 10% to 90%	$A_V = +1, V_{OUT} = 0.1V_{P-P}, R_F = 0\Omega,$		1.1		μs
	Fall Time, t <sub>f</sub> 10% to 90%	$R_L = 10k\Omega$ , $C_L = 1.2pF$		1.1		μs
t <sub>r</sub> , t <sub>f</sub> Large Signal	Rise Time, t <sub>r</sub> 10% to 90%	$A_V = +1$ , $V_{OUT} = 2V_{P-P}$ , $R_F = 0\Omega$ ,		8		μs
	Fall Time, t <sub>f</sub> 10% to 90%	$R_L = 10k\Omega$ , $C_L = 1.2pF$		10		μs
t <sub>s</sub>	Settling Time to 0.1%, 2V <sub>P-P</sub> Step	$A_V$ = +1, $R_F$ = 0 $\Omega$ , $R_L$ = 10k $\Omega$ , $C_L$ = 1.2pF		35		μs

#### NOTES:

- 8. Compliance to datasheet limits is assured by one or more methods: production test, characterization and/or design.
- 9. Parts are 100% tested with a minimum operating voltage of 1.8V to a VOS limit of  $\pm 15 \mu V$ .

## **Typical Performance Curves** v+=5V, v-=0V, $v_{CM}=2.5V$ , $R_L=0$ pen.

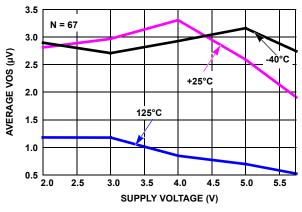


FIGURE 3. AVERAGE INPUT OFFSET VOLTAGE vs SUPPLY VOLTAGE

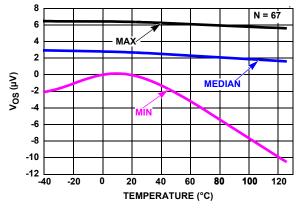


FIGURE 4.  $V_{OS}$  vs TEMPERATURE,  $V_S = \pm 1.0V$ ,  $V_{IN} = 0V$ ,  $R_L = INF$ 

# Typical Performance Curves $V+=5V, V-=0V, V_{CM}=2.5V, R_L=Open.$ (Continued)

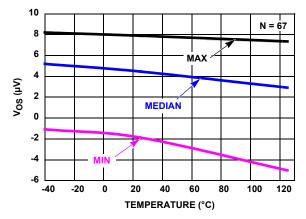


FIGURE 5.  $V_{OS}$  vs TEMPERATURE,  $V_S = \pm 2.5 V$ ,  $V_{IN} = 0 V$ ,  $R_L = INF$ 

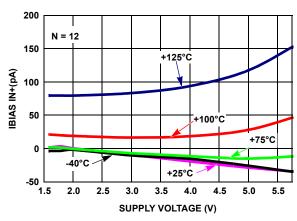


FIGURE 6. IB+ vs SUPPLY VOLTAGE vs TEMPERATURE

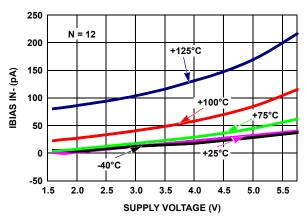


FIGURE 7.  $I_{B^-}$  vs SUPPLY VOLTAGE vs TEMPERATURE

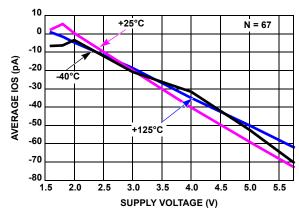


FIGURE 8. IOS vs SUPPLY VOLTAGE vs TEMPERATURE

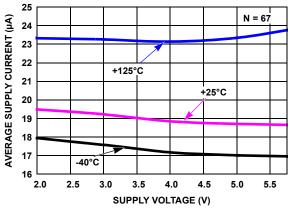


FIGURE 9. AVERAGE SUPPLY CURRENT vs SUPPLY VOLTAGE

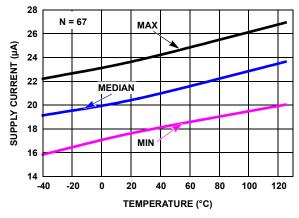


FIGURE 10. MIN/MAX SUPPLY CURRENT vs TEMPERATURE,  $V_S = \pm 0.8 V, V_{IN} = 0 V, \, R_L = INF$ 

# Typical Performance Curves V+=5V, V-=0V, $V_{CM}=2.5V$ , $R_L=0$ pen. (Continued)

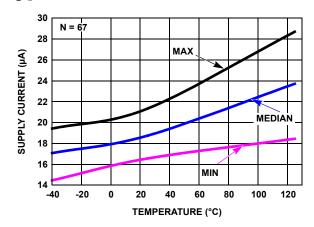


FIGURE 11. MIN/MAX SUPPLY CURRENT vs TEMPERATURE,  $V_S=\pm 2.5 V, V_{IN}=0 V, \, R_L=INF$ 

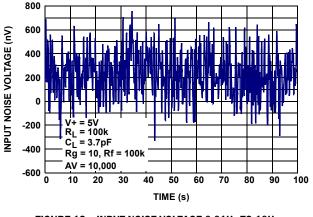


FIGURE 12. INPUT NOISE VOLTAGE 0.01Hz TO 10Hz

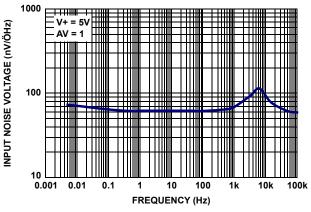


FIGURE 13. INPUT NOISE VOLTAGE DENSITY vs FREQUENCY

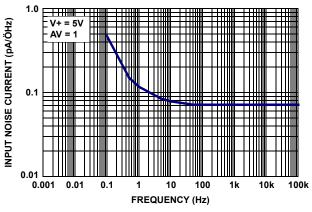


FIGURE 14. INPUT NOISE CURRENT DENSITY vs FREQUENCY

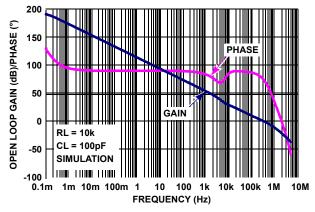


FIGURE 15. FREQUENCY RESPONSE vs OPEN LOOP GAIN,  $R_L = 10k$ 

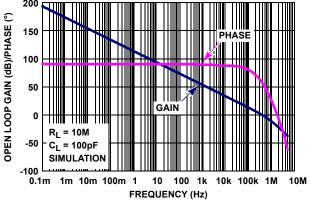


FIGURE 16. FREQUENCY RESPONSE vs OPEN LOOP GAIN,  $R_L = 10M$ 

# **Typical Performance Curves** $V+=5V, V-=0V, V_{CM}=2.5V, R_L=Open.$ (Continued)

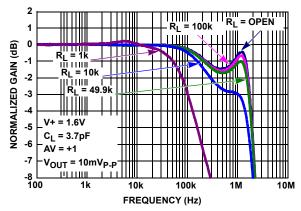


FIGURE 17. GAIN vs FREQUENCY vs  $R_{L_1}V_S = 1.6V$ 

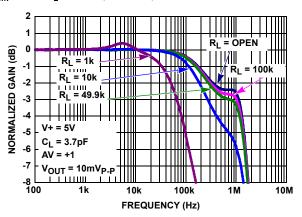


FIGURE 18. GAIN vs FREQUENCY vs  $R_{L}$ ,  $V_S = 5V$ 

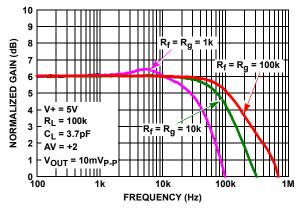


FIGURE 19. GAIN vs FREQUENCY vs FEEDBACK RESISTOR VALUES  $R_{\rm f}/R_{\rm g}$ 

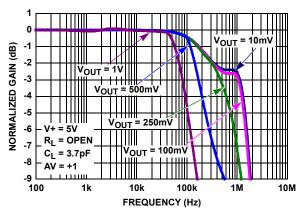


FIGURE 20. GAIN vs FREQUENCY vs V<sub>OUT.</sub> R<sub>L</sub> = OPEN

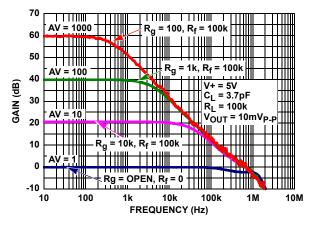


FIGURE 21. FREQUENCY RESPONSE vs CLOSED LOOP GAIN

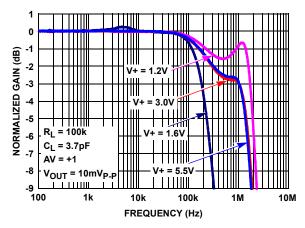


FIGURE 22. GAIN vs FREQUENCY vs SUPPLY VOLTAGE

# Typical Performance Curves V+=5V, V-=0V, $V_{CM}=2.5V$ , $R_L=0$ pen. (Continued)

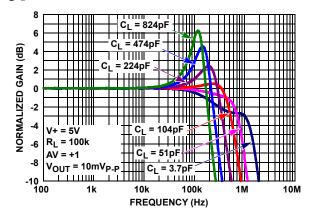


FIGURE 23. GAIN vs FREQUENCY vs CL

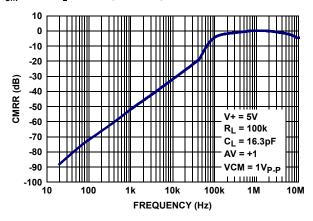


FIGURE 24. CMRR vs FREQUENCY, V<sub>S</sub> = 5V

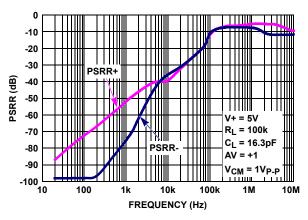


FIGURE 25. PSRR vs FREQUENCY,  $V_S = 5V$ 

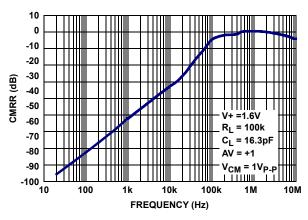


FIGURE 26. CMRR vs FREQUENCY, V<sub>S</sub> = 1.6V

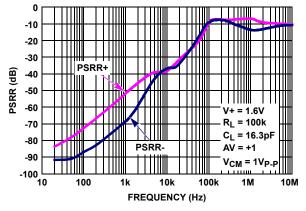


FIGURE 27. PSRR vs FREQUENCY, V<sub>S</sub> = 1.6V

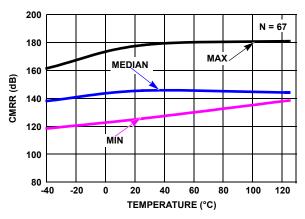


FIGURE 28. CMRR vs TEMPERATURE, VCM = -2.5V TO +2.5V,  $V+=\pm2.5V$ 

# Typical Performance Curves $V+=5V, V-=0V, V_{CM}=2.5V, R_L=Open.$ (Continued)

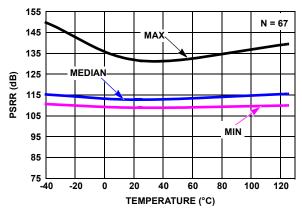


FIGURE 29. PSRR vs TEMPERATURE, V+ = 2V TO 5.5V

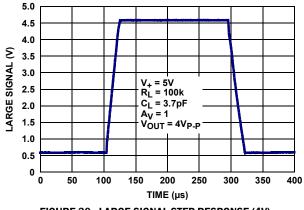


FIGURE 30. LARGE SIGNAL STEP RESPONSE (4V)

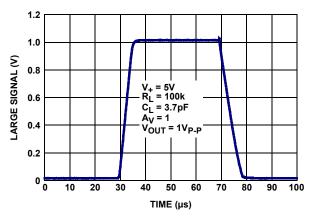


FIGURE 31. LARGE SIGNAL STEP RESPONSE (1V)

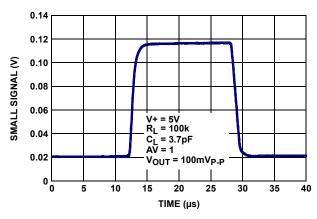


FIGURE 32. SMALL SIGNAL STEP RESPONSE (100mV)

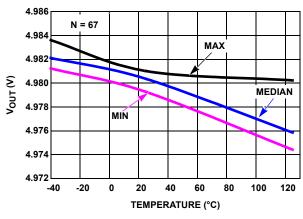


FIGURE 33.  $V_{OUT}$  HIGH vs TEMPERATURE,  $R_L = 10k$ ,  $V_S = 5V$ 

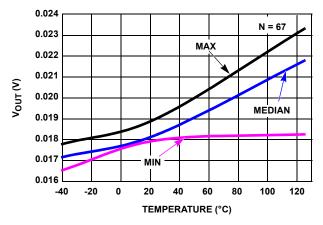


FIGURE 34.  $V_{OUT}$  LOW vs TEMPERATURE,  $R_L$  = 10k,  $V_S$  = 5V

## Typical Performance Curves V+ = 5V, V- = 0V, V<sub>CM</sub> = 2.5V, R<sub>L</sub> = Open. (Continued)

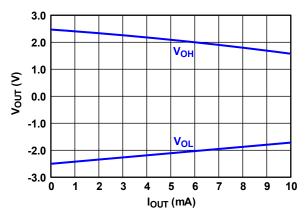


FIGURE 35.  $V_{OH}$ ,  $V_{OL}$  vs  $I_{OUT}$ ,  $V_S = \pm 2.5V$ 

## **Applications Information**

### **Functional Description**

The ISL28133 uses a proprietary chopper-stabilized architecture shown in the "Block Diagram" on page 2. The ISL28133 combines a 400kHz main amplifier with a very high open loop gain (174dB) chopper stabilized amplifier to achieve very low offset voltage and drift (2 $\mu$ V, 0.02 $\mu$ V/°C typical) while consuming only 18 $\mu$ A of supply current per channel.

This multi-path amplifier architecture contains a time continuous main amplifier whose input DC offset is corrected by a parallel-connected, high gain chopper stabilized DC correction amplifier operating at 100kHz. From DC to ~5kHz, both amplifiers are active with DC offset correction and most of the low frequency gain is provided by the chopper amplifier. A 5kHz crossover filter cuts off the low frequency amplifier path leaving the main amplifier active out to the 400kHz gain-bandwidth product of the device.

The key benefits of this architecture for precision applications are very high open loop gain, very low DC offset, and low 1/f noise. The noise is virtually flat across the frequency range from a few mHz out to 100kHz, except for the narrow noise peak at the amplifier crossover frequency (5kHz).

### Rail-to-rail Input and Output (RRIO)

The RRIO CMOS amplifier uses parallel input PMOS and NMOS that enable the inputs to swing 100mV beyond either supply rail. The inverting and non-inverting inputs do not have back-to-back input clamp diodes and are capable of maintaining high input impedance at high differential input voltages. This is effective in eliminating output distortion caused by high slew-rate input signals.

The output stage uses common source connected PMOS and NMOS devices to achieve rail-to-rail output drive capability with 17mA current limit and the capability to swing to within 20mV of either rail while driving a 10k $\Omega$  load.

### **IN+ and IN- Protection**

All input terminals have internal ESD protection diodes to both positive and negative supply rails, limiting the input voltage to within one diode beyond the supply rails. For applications where either input is expected to exceed the rails by 0.5V, an external series resistor must be used to ensure the input currents never exceed 20mA (see Figure 36).

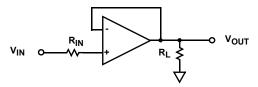


FIGURE 36. INPUT CURRENT LIMITING

### **Layout Guidelines for High Impedance Inputs**

To achieve the maximum performance of the high input impedance and low offset voltage of the ISL28133 amplifiers, care should be taken in the circuit board layout. The PC board surface must remain clean and free of moisture to avoid leakage currents between adjacent traces. Surface coating of the circuit board will reduce surface moisture and provide a humidity barrier, reducing parasitic resistance on the board.

#### **High Gain, Precision DC-Coupled Amplifier**

The circuit in Figure 37 implements a single-stage, 10kV/V DC-coupled amplifier with an input DC sensitivity of under 100nV that is only possible using a low VOS amplifier with high open loop gain. This circuit is practical down to 1.8V due to it's rail-to-rail input and output capability. Standard high gain DC amplifiers operating from low voltage supplies are not practical at these high gains using typical low offset precision op amps because the input offset voltage and temperature coefficient consume most of the available output voltage swing. For example, a typical precision amplifier in a gain of 10kV/V with a  $\pm 100\mu V$  VOS and a temperature coefficient of  $0.5\mu V/$  °C would produce a DC error at the output of >1V with an additional 5mV °C of temperature dependent error. At 3V, this DC error



consumes > 30% of the total supply voltage, making it impractical to measure sub-microvolt low frequency signals.

The  $\pm 8\mu V$  max  $V_{OS}$  and  $0.075\mu V/^{\circ}C$  of the ISL28133 produces a temperature stable maximum DC output error of only  $\pm 80mV$  with a maximum temperature drift of  $0.75mV/^{\circ}C$ . The additional benefit of a very low 1/f noise corner frequency and some feedback filtering enables DC voltages and voltage fluctuations well below 100nV to be easily detected with a simple single stage amplifier.

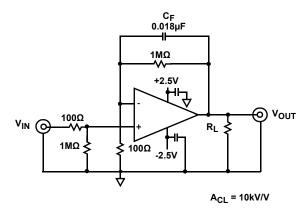


FIGURE 37. HIGH GAIN, PRECISION DC-COUPLED AMPLIFIER

### Long Term Vos Drift

Figure 38 shows a plot of daily  $V_{OS}$  drift measurements of 30 individual ISL28133 amplifiers over a continuous 572 day period at +25 °C. The 30 units were connected in a gain of 10k, mounted on a single PC board and kept at room temp. The 30 amplifier outputs were measured daily by a DVM and scanner under computer control. The daily  $V_{OS}$  measurements were subtracted from the initial  $V_{OS}$  value to calculate the  $V_{OS}$  shift. The test board was powered from a UPS to maintain uninterrupted power to the test units. Three instances of lost measurement data ranging from 2 days to 2 weeks due to power loss to the measurement scanner were detected, and data were interpolated.

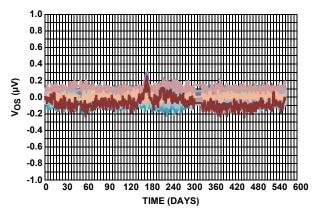


FIGURE 38. LONG TERM DRIFT (VOS vs TIME) FOR 30 UNITS

The change in amplifier  $V_{OS}$  over the 572 day period for all 30 amplifiers (see Figure 39) was less than  $\pm 100$ nV, and no clear  $V_{OS}$  long term drift trend was evident in the data. The excellent long term drift performance is a result of the chopper amplifier's ability to measure and correct  $V_{OS}$  errors, leaving only the  $V_{OS}$  error contribution due to changes in the long term stability of the external components (see Figure 40).

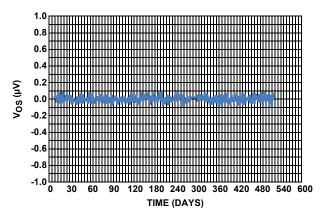


FIGURE 39. LONG TERM DRIFT (VOS vs TIME) FOR A SINGLE UNIT

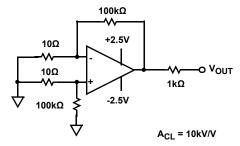


FIGURE 40. LONG TERM DRIFT TEST CIRCUIT

#### **ISL28133 SPICE Model**

Figure 41 shows the SPICE model schematic and Figure 42 shows the net list for the ISL28133 SPICE model. The model is a simplified version of the actual device and simulates important parameters such as noise, Slew Rate, Gain and Phase. The model uses typical parameters from the ISL28133. The poles and zeros in the model were determined from the actual open and closed-loop gain and phase response. This enables the model to present an accurate AC representation of the actual device. The model is configured for ambient temperature of +25°C.

Figures 43 through 50 show the characterization vs simulation results for the Noise Density, Frequency Response vs Close Loop Gain, Gain vs Frequency vs CL and Large Signal Step Response (4V).

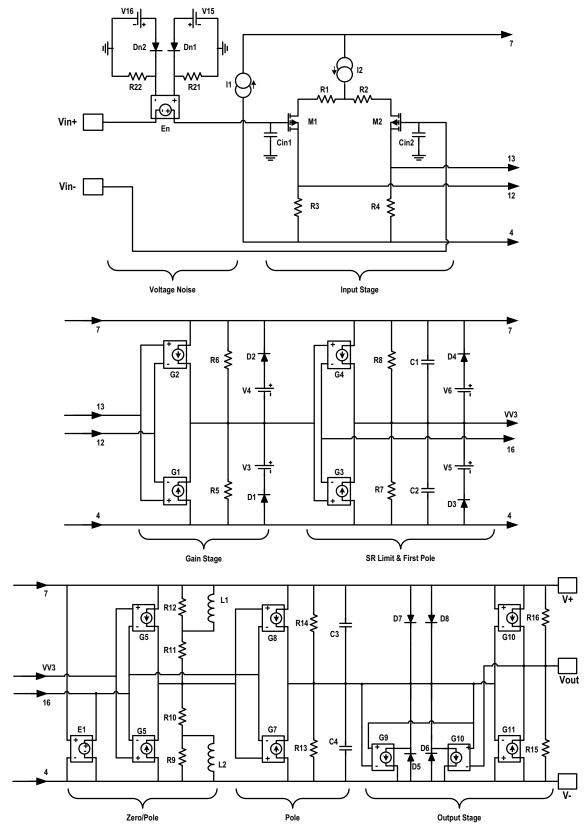


FIGURE 41. SPICE CIRCUIT SCHEMATIC

```
* ISL28133 Macromodel
                                                           V_V6
                                                                     18 VV3 0.7Vdc
* Revision B, April 2009
* AC characteristics, Voltage Noise
                                                           *Zero/Pole
* Connections:
                     +input
                                                           E E1
                                                                     16 4 7 4 0.5
                                                           G G5
                                                                     4 VV4 VV3 16 0.000001
                          -input
                               +Vsupply
                                                                     7 VV4 VV3 16 0.000001
                                                           G G6
                                     -Vsupply
                                                           L L1
                                                                    20 7 0.3H
                                          output
                                                           R R12
                                                                     20 7 2.5meg
                                                           R R11
                                                                     VV4 20 1meg
.subckt ISL28133
                     3
                          2
                               7
                                     4
                                          6
                                                           L L2
                                                                    4 19 0.3H
                                                                     4 19 2.5meg
                                                           R R9
*Voltage Noise
                                                           R R10
                                                                     19 VV4 1meg
D DN1
           102 101 DN
                                                           *Pole
D DN2
           104 103 DN
                                                           G G7
                                                                     4 VV5 VV4 16 0.000001
R R21
           0 101 120k
                                                           G G8
                                                                     7 VV5 VV4 16 0.000001
R R22
           0 103 120k
                                                           C_C3
                                                                     VV5 7 0.12p
E EN
          8 3 101 103 1
                                                           C C4
                                                                     4 VV5 0.12p
V V15
                                                           R R13
          102 0 0.1Vdc
                                                                     4 VV5 1meg
V_V16
           104 0 0.1Vdc
                                                           R R14
                                                                     VV5 7 1meg
*Input Stage
                                                           *Output Stage
C Cin1
           80 0.4p
                                                           G G9
                                                                      21 4 6 VV5 0.0000125
C Cin2
                                                           G G10
                                                                      22 4 VV5 6 0.0000125
           20 2.0p
R R1
          9 10 10
                                                           D D5
                                                                     4 21 DY
                                                                     4 22 DY
R<sub>R2</sub>
          10 11 10
                                                           D D6
R R3
         4 12 100
                                                           D D7
                                                                     7 21 DX
R R4
          4 13 100
                                                           D D8
                                                                     7 22 DX
M M1
          12899 pmosisil
                                                           R R15
                                                                      46 8k
+ L=50u
                                                           R R16
                                                                      67 8k
+ W=50u
                                                           G G11
                                                                      6 4 VV5 4 -0.000125
M M2
          13 2 11 11 pmosisil
                                                           G G12
                                                                      7 6 7 VV5 -0.000125
+ L=50u
+ W=50u
                                                           .model pmosisil pmos (kp=16e-3 vto=10m)
I 11
        4 7 DC 92uA
                                                           .model DN D(KF=6.4E-16 AF=1)
        7 10 DC 100uA
                                                           .MODEL DX D(IS=1E-18 Rs=1)
1 12
                                                           .MODEL DY D(IS=1E-15 BV=50 Rs=1)
*Gain stage
                                                           .ends ISL28133
G G1
          4 VV2 13 12 0.0002
G G2
          7 VV2 13 12 0.0002
R R5
         4 VV2 1.3Meg
R R6
         VV2 7 1.3Meg
D D1
         4 14 DX
D D2
         15 7 DX
V V3
         VV2 14 0.7Vdc
V_V4
         15 VV2 0.7Vdc
*SR limit first pole
G_G3
          4 VV3 VV2 16 1
          7 VV3 VV2 16 1
G G4
R R7
         4 VV3 1meg
R R8
          VV3 7 1meg
C_C1
         VV3 7 12u
C C2
         4 VV3 12u
D D3
         4 17 DX
D D4
          18 7 DX
```

FIGURE 42. SPICE NET LIST

V V5

VV3 17 0.7Vdc

## **Characterization vs Simulation Results**

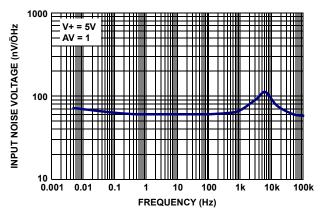


FIGURE 43. CHARACTERIZED INPUT NOISE VOLTAGE DENSITY vs FREQUENCY

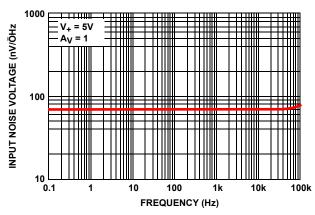


FIGURE 44. SIMULATED INPUT NOISE VOLTAGE DENSITY vs FREQUENCY

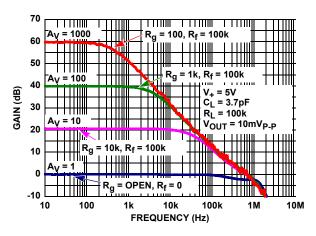


FIGURE 45. CHARACTERIZED FREQUENCY RESPONSE vs CLOSED LOOP GAIN

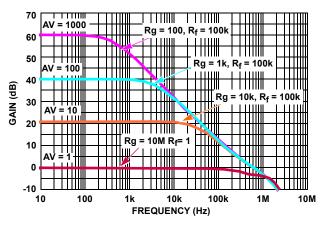


FIGURE 46. SIMULATED FREQUENCY RESPONSE vs CLOSED LOOP GAIN

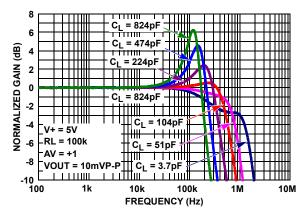


FIGURE 47. CHARACTERIZED GAIN vs FREQUENCY vs CL

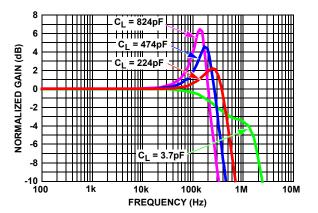


FIGURE 48. SIMULATED GAIN vs FREQUENCY vs CL

# Characterization vs Simulation Results (Continued)

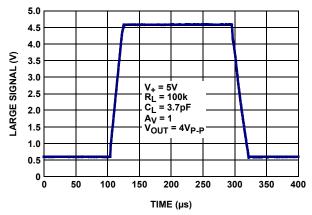


FIGURE 49. CHARACTERIZED LARGE SIGNAL STEP RESPONSE (4V)

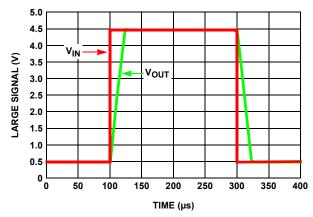


FIGURE 50. SIMULATED LARGE SIGNAL STEP RESPONSE (4V)

# **Revision History**

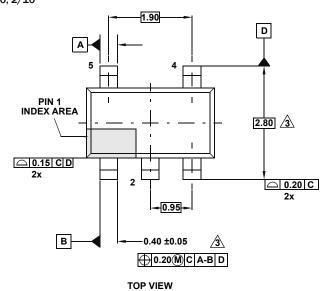
The revision history provided is for informational purposes only and is believed to be accurate, but not warranted. Please go to web to make sure you have the latest Rev.

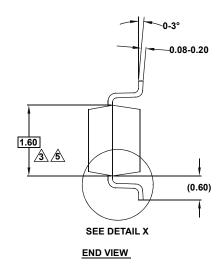
DATE	REVISION	CHANGE
Apr 22, 2021	7.1	Removed retired part and applicable package information from document.  Updated the titles for Figure 33 and Figure 34.  Added Figure 35.  Removed About Intersil section
Sep 16, 2015	7.0	Updated Ordering Information table on page 2. Updated About Intersil Verbiage.
Feb 19, 2014	6.0	Updated location of note references. Added ISL28133CSENSEV1Z to ordering information table on page 2.
May 31, 2011	5.0	Changed minimum operating supply voltage from +1.65V to +1.8V throughout entire datasheet.  Added Tjc information for 5 Ld SOT-23 package in Thermal information on page 5.
Feb 1, 2011	4.0	-Converted to Updated Intersil TemplatePage 1 Graphics numbered as Figures 1 and 2Updated Ordering Information on page 2 by adding part ISL28133FHZ-T7AChanged Note on page 5, which read "Parameters with MIN and/or MAX limits are 100% tested at +25°C, unless otherwise specified. Temperature limits established by characterization and are not production tested." to "Compliance to datasheet limits is assured by one or more methods: production test, characterization and/or design." -Added two Long Term Drift Curves (Figures 38 and 39) and section "Long Term VOS Drift" on page 12 -Replaced POD MDP0038 (no dimension changes), now obsolete with P5.064A.
May 3, 2010	3.0	Title Page 1: Replaced "Zero-Drift" with "Chopper Stabilized" for title and part description On page 3: Pin Configuration: MTDFN -> uTDFN On page 7: Figure 12: Changed 0.1Hz to 0.01Hz in Figure caption On page 11: In "Functional Description"; Paragraph 1, 2nd sentence: Changed text from "open loop gain (200dB)" -to- "open loop gain (174dB)" Changed TYP for "Open Loop Gain" on page 4 from 200dB to 174dB. On page 11: In "High Gain, Precision DC-Coupled Amplifier"; Paragraph 2, 1st sentence: Changed text from "DC output error of only ±80mV with a maximum temperature drift of 0.75μV/°C." to " DC output error of only ±80mV with a maximum temperature drift of 0.75mV/C." Removed "Coming Soon" from ISL28133EVAL1Z in the ordering information table on pg 2.
Sep 24, 2009	2.0	Converted to new Intersil template. Removed ISL28233 and ISL28433 from data sheet, added Applications, Related Literature, Typical Application Circuit, Performance Curve, updated ordering information by removing "coming soon" on SC70 and uTDFN packages and adding Eval board listed as "coming soon". Added Block Diagram, Changed in Abs Max Rating Voltage from "5.75V" to "6.5V". Removed Tjc from Thermal Information until provided by packaging scheduled for 9-11-09. Changed Low Offset "drift" to Low Offset "TC", added Max Junction Temp 140C, added SPICE model and simulation results, removed supply current graph at +-3V, re-ordered typical performance curves, removed guard ring information from application section. Added Revision History and Products Information
May 29, 2009	1.0	Page 4: Removed the RL = 100 Curve from Figures 3, 4 and 5. Page 1: Under Features, removed the word "Output" from "Low Output Noise"
Mar 25, 2009	0.0	Initial Release

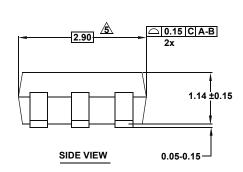


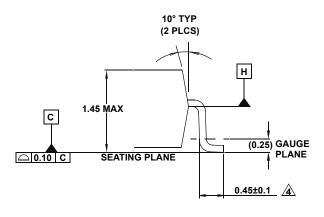
# **Package Outline Drawings**

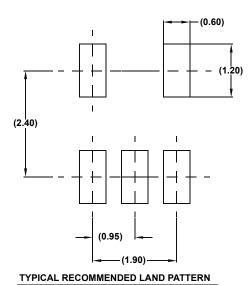
P5.064A 5 Lead Small Outline Transistor Plastic Package Rev 0, 2/10











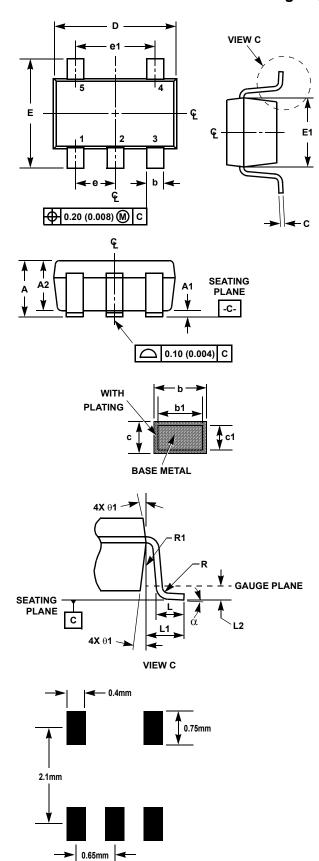
NOTES:

Dimensions are in millimeters.
 Dimensions in ( ) for Reference Only.

DETAIL "X"

- 2. Dimensioning and tolerancing conform to ASME Y14.5M-1994.
- 3. Dimension is exclusive of mold flash, protrusions or gate burrs.
- 4. Foot length is measured at reference to guage plane.
- 5. This dimension is measured at Datum "H".
- 6. Package conforms to JEDEC MO-178AA.

## Small Outline Transistor Plastic Packages (SC70-5)



**P5.049**5 LEAD SMALL OUTLINE TRANSISTOR PLASTIC PACKAGE

	INC	HES	MILLIMETERS		
SYMBOL	MIN	MAX	MIN	MAX	NOTES
Α	0.031	0.043	0.80	1.10	-
A1	0.000	0.004	0.00	0.10	-
A2	0.031	0.039	0.80	1.00	-
b	0.006	0.012	0.15	0.30	-
b1	0.006	0.010	0.15	0.25	
С	0.003	0.009	0.08	0.22	6
c1	0.003	0.009	0.08	0.20	6
D	0.073	0.085	1.85	2.15	3
E	0.071	0.094	1.80	2.40	-
E1	0.045	0.053	1.15	1.35	3
е	0.0256 Ref		0.65	Ref	-
e1	0.051	0.0512 Ref		Ref	-
L	0.010	0.018	0.26	0.46	4
L1	0.017	7 Ref.	0.420	Ref.	-
L2	0.006	BSC	0.15	BSC	
α	0°	8°	0°	8°	-
N	5			5	5
R	0.004	-	0.10	-	
R1	0.004	0.010	0.15	0.25	

Rev. 3 7/07

### NOTES:

- 1. Dimensioning and tolerances per ASME Y14.5M-1994.
- 2. Package conforms to EIAJ SC70 and JEDEC MO-203AA.
- 3. Dimensions D and E1 are exclusive of mold flash, protrusions, or gate burrs.
- 4. Footlength L measured at reference to gauge plane.
- 5. "N" is the number of terminal positions.
- 6. These Dimensions apply to the flat section of the lead between 0.08mm and 0.15mm from the lead tip.
- 7. Controlling dimension: MILLIMETER. Converted inch dimensions are for reference only.

TYPICAL RECOMMENDED LAND PATTERN

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